

TECHNICAL DATA DATA SHEET 4756, REV. B

POWER SCHOTTKY RECTIFIER Very Low Reverse Leakage

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra Low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	60	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	120	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave (per leg)	1650	A
Non-Repetitive Avalanche Energy	E _{AS}	$T_J = 25 \text{ °C}, I_{AS} = 1.3 \text{ A},$ L = 40mH (per leg)	27	mJ
Repetitive Avalanche Current	I _{AR}	I_{AS} decay linearly to 0 in 1 µs f limited by T _J max V _A =1.5V _R	1.3	A
Thermal Resistance (per leg)	R _{thJC}	Per Package	0.38	°C/W
Max. Junction Temperature	TJ	-	-65 to +175	°C
Max. Storage Temperature	T _{stg}	-	-65 to +175	۵°

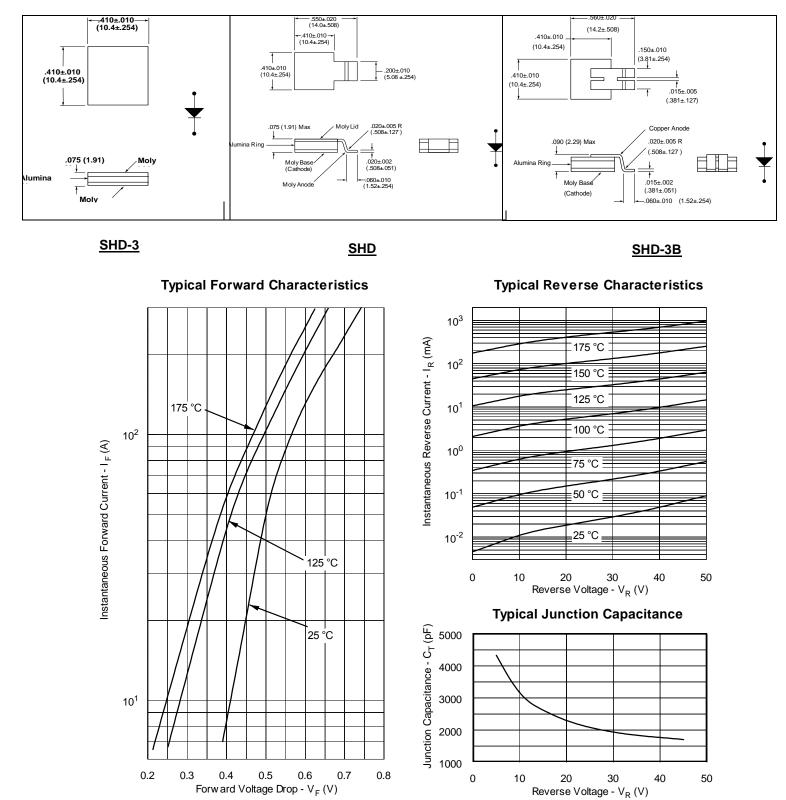
Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 120A, Pulse, T _J = 25 °C	0.70	V
		(per leg) measured at the leads		
	V _{F2}	@ 120A, Pulse, T _J = 125 °C	0.67	V
		(per leg) measured at the leads		
Max. Reverse Current	I _{R1}	$@V_R = 60V$, Pulse,	11	mA
		$T_J = 25 \ ^{\circ}C \ (per leg)$		
	I _{R2}	$@V_R = 60V$, Pulse,	840	mA
		$T_J = 125 \ ^{\circ}C$ (per leg)		
Max. Junction Capacitance	CT	@V _R = 5 V, T _C = 25 °C	4800	pF
		f _{SIG} = 1 MHz,		
		$V_{SIG} = 50 \text{mV} (\text{p-p}) (\text{per leg})$		

SENSITRON

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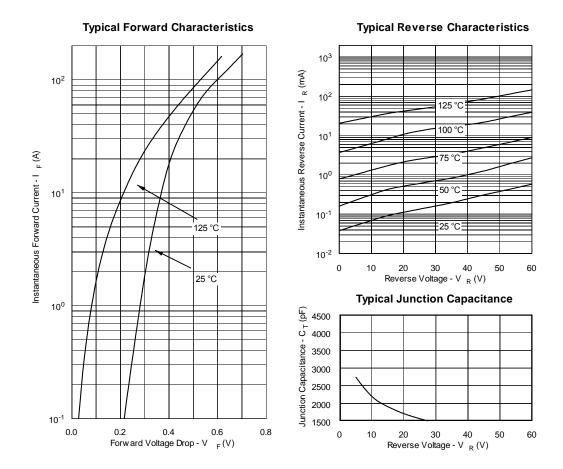
Mechanical Dimensions: in inches / mm



Vf Curves shown are for die only.

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